

MS32 Switching Sensor



- AMR Switching-Sensor
- TDFN Outline 2.5x2.5x0.8 mm³
- Temperature Compensated Switching Point
- Low Power Consumption

DESCRIPTION

The MS32 is a magnetic field sensor which is built in the form of a Wheatstone bridge. Each of its four resistors is made from *Permalloy*, a material that shows the *anisotropic magneto resistance effect*. An unidirectional magnetic field in the surface parallel to the chip (x-y plane) along the y-axis will deliver a field dependent output signal. A **magnetic switching point**, which is almost **independent on temperature** is typically set to $H_s=1.85$ kA/m. In addition, the characteristic curve is linear over a wide magnetic field range. Thus, the new MS32 simplifies the adaption of the sensor to different mechanical and magnetical environments. The sensor die is packaged in a TDFN package.

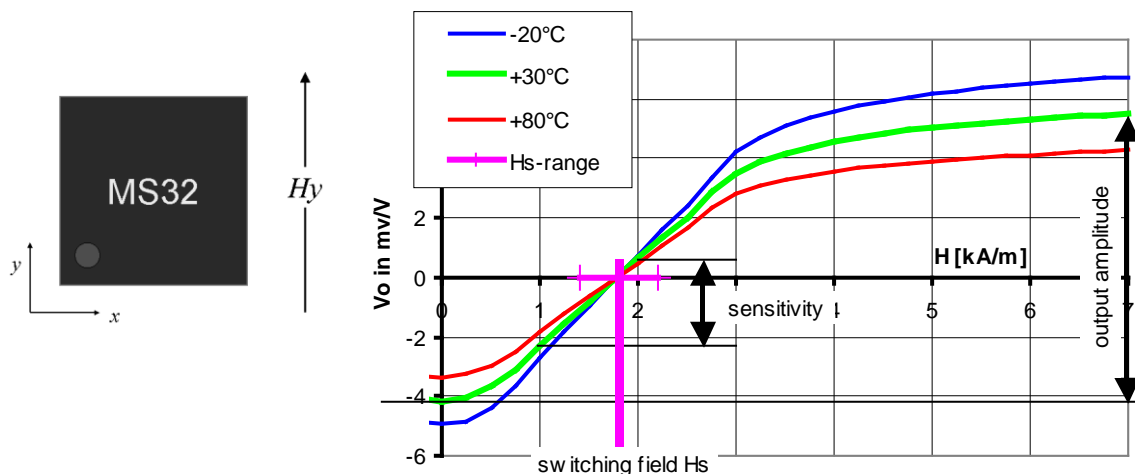


Figure 1: Characteristic curves for MS32 at different ambient temperatures (-20°C, +30°C, +80°C)

FEATURES

- Sensor based on solid state magnetoresistance effect
- Unipolar signal output
- Linear field response
- High sensitivity, low hysteresis
- Temperature compensated switching point
- Low power consumption due to high bridge resistance
- Supply voltage up to 30 V
- Small TDFN package

APPLICATIONS

- Contactless position detection (presence, open/close)
 - Industrial
 - Consumer
 - Automotive
- Applications, like:
- Small stroke pneumatic cylinders
 - Cover positions of Notebooks and Mobiles
 - Doors, windows etc.

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CHARACTERISTIC VALUES

Parameter	Condition	Symbol	Min	Typ	Max	Unit
Mechanical dimensions						
Length		X		2.5		mm
Width		Y		2.5		mm
Height		Z		0.75		mm
Pad size	7)			0.25 x 0.30		mm ²
Operating limits						
Max. supply voltage		V _{CC, MAX}			30	V
Temp. compensation range		T _{COMP}	-25		+85	°C
Operating temperature		T _{OP}	-45		+125	°C
Storage temperature		T _{ST}	-45		+150	°C

Stress above one or more of the limiting values may cause permanent damage to the device. Exposure to limiting values for extended periods may affect device reliability.

Parameter	Condition	Symbol	Min	Typ	Max	Unit
Sensor specification (V_{CC} = 5 V, T = 30 °C)						
Supply voltage		V _{CC}		5	30	V
Resistance		R _B	10300	11500		Ω
Offset		V _{OFF} /V _{CC}		-4	-1.5	mV/V
Sensitivity	1)	S	2	3		(mV/V)/(kA/m)
Output amplitude	2)	V _{MAX}	8			mV/V
Hysteresis (@ V ₀ =0) 3)		Hyst.			0.9	mV/V
Sensor specification (T = -25 °C; +85 °C; Conditions A & B) 6)						
TC of amplitude		TCSV	-0.36	-0.32	-0.28	%/K
TC of bridge resistance		TCBR	+0.27	+0.32	+0.37	%/K
Switching field 5)	4)	H _s	1.40	1.85	2.30	kA/m

All parameters are measured on wafer level.

- 1) average gradient in the range 1.0 - 2.0 kA/m
- 2) difference between output voltage/supply voltage measured at H = 7 kA/m and H = 0 kA/m
- 3) hysteresis [in kA/m] = hysteresis [in mV/V] / S
- 4) switching voltage = 0 mV/V
- 5) switching field = magnetic field at switching voltage
- 6) values at -25°C can be determined by linear extrapolation from +30°C- and +85°C-values.
- 7) recommended solder reflow process according to IPC/JEDEC J-STD-020D (Pb-Free Process)